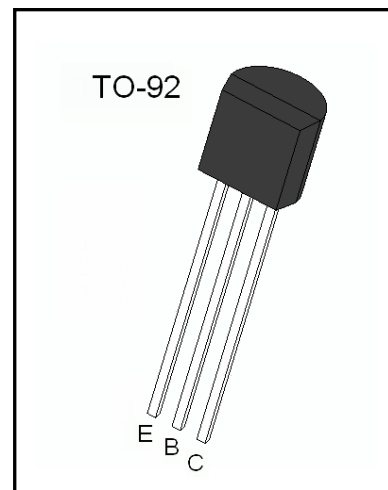


High Voltage Transistor

- Collector-Emitter Voltage: $V_{CEO}=350V$
- Collector Dissipation: $P_{C(max)}=625mW$
- Complement to 2N6520

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV_{CBO}	350	V
Collector-Emitter Voltage	BV_{CEO}	350	V
Emitter-Base Voltage	BV_{EBO}	6	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_D	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C


Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BV_{CBO}	$I_C = 100\mu A, I_E = 0$	350			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 1mA, I_B = 0$	350			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 100\mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 250V, I_E = 0$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			50	nA
DC current gain	h_{FE}	$V_{CE} = 10V, I_B = 30mA$ $V_{CE} = 10V, I_B = 30mA$	30 20		200 200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30mA, I_B = 3mA$ $I_C = 50mA, I_B = 5mA$			0.5 1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 30mA, I_B = 3mA$			0.9	V
Transition frequency	f_T	$V_{CE} = 20V, I_B = 10mA$	40			MHz

Package Dimensions (Unit:mm)

